Special Issue

High-Density Solid-State Memory Devices and Technologies

Message from the Guest Editors

The relevance of solid-state memory technologies in the world of electronics is on the constant rise. Due to their continuously increasing integration density and their unmatched performance, solid-state memory technologies are currently not only gaining importance in the arena of data storage but are also offering the opportunity for new memory-centric computing scenarios. 3-D NAND Flash memory, phase-change memory (PCM), resistive random-access memory (ReRAM), magnetoresistive random-access memory (MRAM), and ferroelectric memory are the most important players at the heart of this memory revolution, along with dynamic random-access memory (DRAM) and static random-access memory (SRAM).

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Deadline for manuscript submissions

closed (30 September 2021)

Electronics

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Impact Factor 2.6
CiteScore 6.1

mdpi.com/si/61929

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Message from the Editor-in-Chief

Electronics is a multidisciplinary journal designed to appeal to a diverse audience of research scientists, practitioners, and developers in academia and industry. The journal is devoted to fast publication of latest technological breakthroughs, cutting-edge developments, and timely reviews of current and emerging technologies related to the broad field of electronics. Experimental and theoretical results are published as regular peer-reviewed articles or as articles within Special Issues guest-edited by leading experts in selected topics of interest.

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